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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/743,151	12/23/2003	Naoki Makita	7040.13	7501
54072 75	11/03/2005		EXAMINER	
SHARP KABUSHIKI KAISHA			BOOTH, RICHARD A	
C/O KEATING & BENNETT, LLP 8180 GREENSBORO DRIVE		ART UNIT	PAPER NUMBER	
SUITE 850			2812	
MCLEAN, VA	22102		DATE MAILED: 11/03/2005	5

Please find below and/or attached an Office communication concerning this application or proceeding.

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		Application No.	Applicant(s)			
Office Action Summary		10/743,151	MAKITA, NAOKI			
		Examiner	Art Unit			
		Richard A. Booth	2812			
Period f	The MAILING DATE of this communication a or Reply	appears on the cover sheet	with the correspondence ac	idress		
WHIO - External after af	IORTENED STATUTORY PERIOD FOR REF CHEVER IS LONGER, FROM THE MAILING ensions of time may be available under the provisions of 37 CFR r SIX (6) MONTHS from the mailing date of this communication. O period for reply is specified above, the maximum statutory periure to reply within the set or extended period for reply will, by state reply received by the Office later than three months after the managed patent term adjustment. See 37 CFR 1.704(b).	DATE OF THIS COMMU 1.136(a). In no event, however, may od will apply and will expire SIX (6) No tute, cause the application to become	NICATION. y a reply be timely filed MONTHS from the mailing date of this ce ABANDONED (35 U.S.C. § 133).	·		
Status						
1) 🔀	Responsive to communication(s) filed on 24	October 2005				
		his action is non-final.				
3)	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.					
Disposit	ion of Claims					
5)□ 6)⊠ 7)□	Claim(s) 1-69 is/are pending in the application of the above claim(s) 1-21,27,28,34,43,44 Claim(s) is/are allowed. Claim(s) 22-26,29-33,35-42,44,46,47,49 and Claim(s) is/are objected to. Claim(s) are subject to restriction and	45,48,50-61 and 67-69 is/ d 62-66 is/are rejected.	are withdrawn from conside	ration.		
Applicat	ion Papers					
10)	The specification is objected to by the Examination The drawing(s) filed on is/are: a) a Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct The oath or declaration is objected to by the	ccepted or b) objected he drawing(s) be held in abe ection is required if the draw	yance. See 37 CFR 1.85(a).			
Priority	under 35 U.S.C. § 119					
12) <u>□</u> a)	Acknowledgment is made of a claim for forei All b) Some * c) None of: 1. Certified copies of the priority docume 2. Certified copies of the priority docume 3. Copies of the certified copies of the priority docume application from the International Bure See the attached detailed Office action for a light	ents have been received. ents have been received in riority documents have be eau (PCT Rule 17.2(a)).	n Application No en received in this National	Stage		
2) Noti 3) Info	nt(s) ce of References Cited (PTO-892) ce of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO-1449 or PTO/SB/er No(s)/Mail Date 1203,1005.	Paper I	ew Summary (PTO-413) No(s)/Mail Date of Informal Patent Application (PTo	O-152)		

DETAILED ACTION

Election/Restrictions

Applicant's election of embodiment 3 in the reply filed on 10/24/05 is acknowledged. Because applicant did not distinctly and specifically point out the supposed errors in the restriction requirement, the election has been treated as an election without traverse (MPEP § 818.03(a)).

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 22-26, 29-33, 36-42, 47, 63, and 65-66 are rejected under 35 U.S.C. 102(b) as being anticipated by Tanaka et al., U.S. Patent 6,251,712.

Tanaka et al. shows the invention as claimed including a method for fabricating a semiconductor device, comprising the steps of: providing an amorphous semiconductor film including a catalyst element of nickel in at least a portion thereof, the catalyst element being capable of promoting crystallization of the amorphous semiconductor film (see col. 4-lines 16-20); performing a first heat treatment on the amorphous semiconductor film so as to crystallize at least a portion of the amorphous semiconductor film, thereby obtaining a crystalline region (see col. 4-lines 21-25); patterning the semiconductor film to form an island-shaped semiconductor layer

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including the crystalline region (see col. 4-lines 55-61); forming a gate insulating film 106 on the island-shaped semiconductor layer; selectively thinning or selectively removing a portion of the gate insulating film that is located outside a region of the island-shaped semiconductor layer where a channel region, a source region and a drain region are formed (see fig. 4E); forming a gettering region capable of attracting the catalyst element in a region where the gate insulating film on the island-shaped semiconductor layer has been thinned or removed (see figs. 4E-4F); simultaneously doping the crystalline region of the island-shaped semiconductor layer with an impurity for forming the source region and the drain region (423,424,425,426); and performing a second heat treatment by laser so as to move at least a portion of the catalyst element in the island-shaped semiconductor layer to the gettering region (see fig. 4G).

With respect to claim 23, note that the implantation of the gettering elements will form an amorphous region in the island layer.

Concerning claim 25, note that both n and p type dopants are implanted prior to the second heat treatment.

Regarding claim 31, note that the gettering regions (417,418,428,429) are at a higher concentration than the source and drain regions.

With respect to claims 32-33, the gettering elements are boron and phosphorous.

Concerning claim 39, after the second heat treatment a line 435 is formed in contact with the source or drain regions.

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Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 35, 44, 46, and 62 are rejected under 35 U.S.C. 103(a) as being unpatentable over Tanaka et al., U.S. Patent 6,251,712.

Tanaka et al. is applied as above but does not expressly disclose particular concentrations and particular sequences of processing steps. However, a prima facie case of obviousness exists because the selection of any order of performing process steps is prima facie obvious in the absence of new or unexpected results, and with respect to the concentration, where the general conditions of a claim are disclosed in the prior art, it is not inventive to discover the optimum or workable ranges by routine experimentation." In re Aller, 220 F.2d 454, 456, 105 USPQ 233, 235 (CCPA 1955).

Claim 64 is rejected under 35 U.S.C. 103(a) as being unpatentable over Tanaka et al., U.S. Patent 6,251,712 in view of Zhang et al., U.S. Patent 5,481,121.

Tanaka et al. is applied as above but does not expressly disclose wherein the catalyst element is selectively doped using a mask.

Zhang et al. discloses selective adding nickel to a region 100 using a mask 103 (see figs. 2A-2B and their description). In view of this disclosure, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify

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the process of Tanaka et al. so as to add the catalyst element selectively as suggested by Zhang et al. because this allows for greater controllability with respect to the crystallization of the semiconductor film.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Richard A. Booth whose telephone number is (571) 272-1668. The examiner can normally be reached on Monday-Thursday from 7:30-6:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Michael Lebentritt can be reached on (571) 272-1873. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Richard A. Booth Primary Examiner Art Unit 2812